



**Advanced Power
Electronics Corp.**

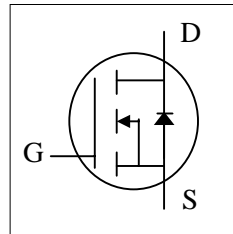
AP60U03GH

RoHS-compliant Product

N-CHANNEL ENHANCEMENT MODE

POWER MOSFET

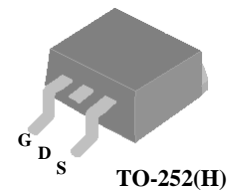
- ▼ Low On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic



BV_{DSS}	30V
$R_{DS(ON)}$	12m Ω
I_D	40A

Description

The Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.



The TO-252 package is universally preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters.

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ C$	Continuous Drain Current	40	A
$I_D@T_C=100^\circ C$	Continuous Drain Current	29	A
I_{DM}	Pulsed Drain Current ¹	140	A
$P_D@T_C=25^\circ C$	Total Power Dissipation	25	W
	Linear Derating Factor	0.2	W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Value	Units
Rthj-c	Thermal Resistance Junction-case	Max. 5.0	$^\circ C/W$
Rthj-a	Thermal Resistance Junction-ambient	Max. 110	$^\circ C/W$



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Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	30	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =10V, I _D =24A	-	-	12	mΩ
		V _{GS} =4.5V, I _D =16A	-	-	24	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	1	-	3	V
g _{fs}	Forward Transconductance	V _{DS} =10V, I _D =30A	-	28	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =30V, V _{GS} =0V	-	-	1	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±20V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =30A	-	13	21	nC
Q _{gs}	Gate-Source Charge	V _{DS} =24V	-	2.2	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =4.5V	-	9	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =15V	-	7	-	ns
t _r	Rise Time	I _D =30A	-	91	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω, V _{GS} =10V	-	18	-	ns
t _f	Fall Time	R _D =0.5Ω	-	10	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	700	1120	pF
C _{oss}	Output Capacitance	V _{DS} =25V	-	155	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	150	-	pF

Source-Drain Diode

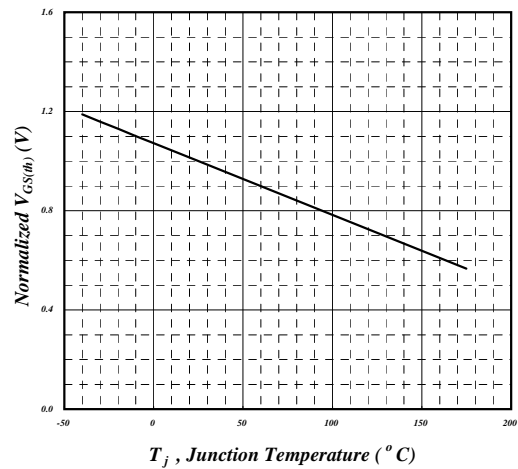
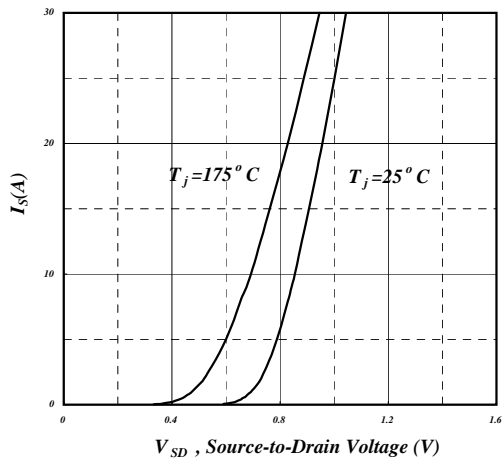
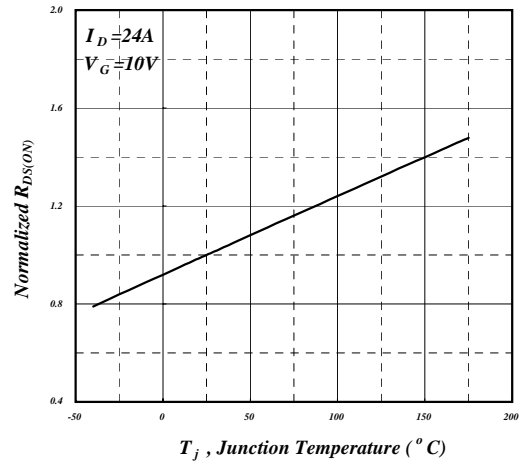
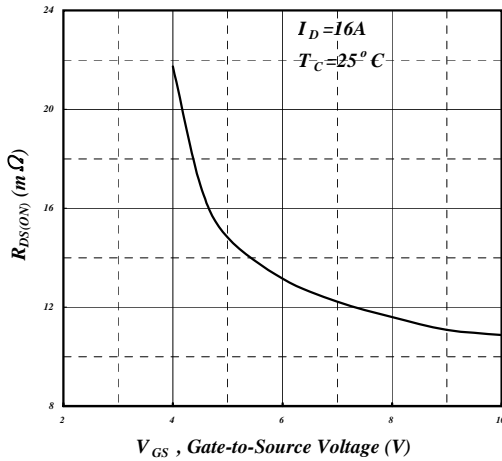
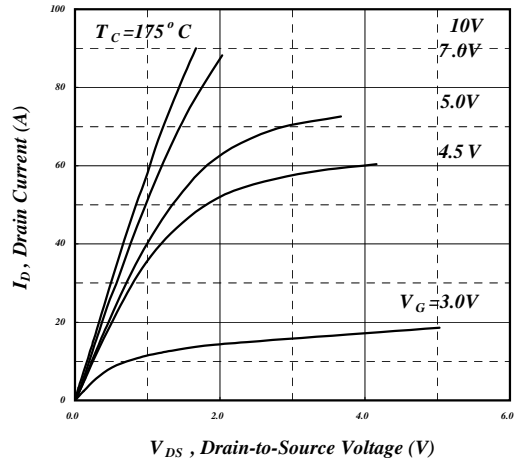
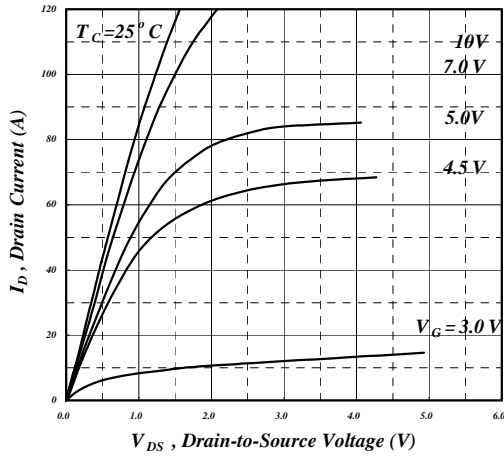
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =24A, V _{GS} =0V	-	-	1.2	V
t _{rr}	Reverse Recovery Time ²	I _S =10A, V _{GS} =0V,	-	23	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	12	-	nC

Notes:

- 1.Pulse width limited by Max. junction temperature
- 2.Pulse test

THIS PRODUCT IS AN ELECTROSTATIC SENSITIVE, PLEASE HANDLE WITH CAUTION.

THIS PRODUCT HAS BEEN QUALIFIED FOR CONSUMER MARKET. APPLICATIONS OR USES AS CRITERIAL COMPONENT IN LIFE SUPPORT DEVICE OR SYSTEM ARE NOT AUTHORIZED.



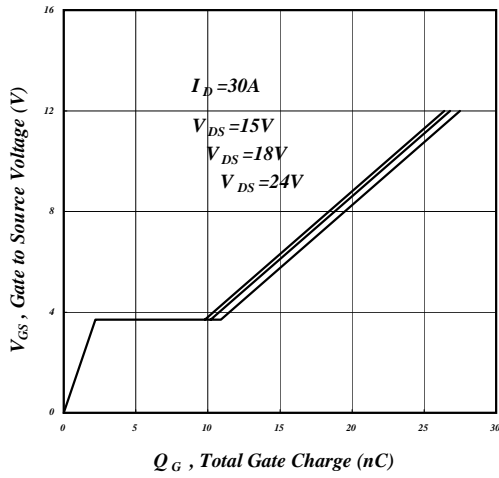


Fig 7. Gate Charge Characteristics

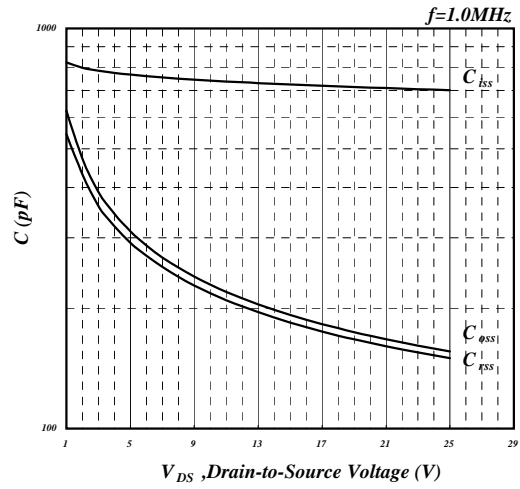


Fig 8. Typical Capacitance Characteristics

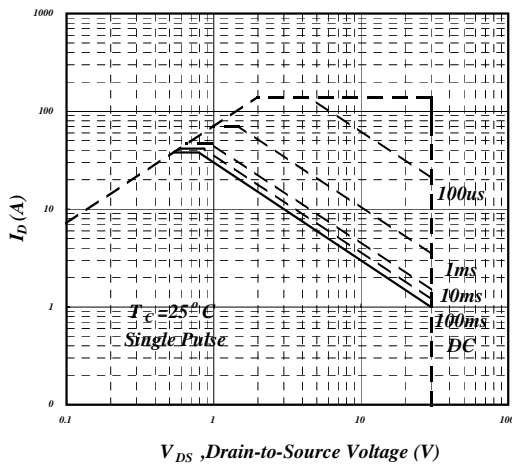


Fig 9. Maximum Safe Operating Area

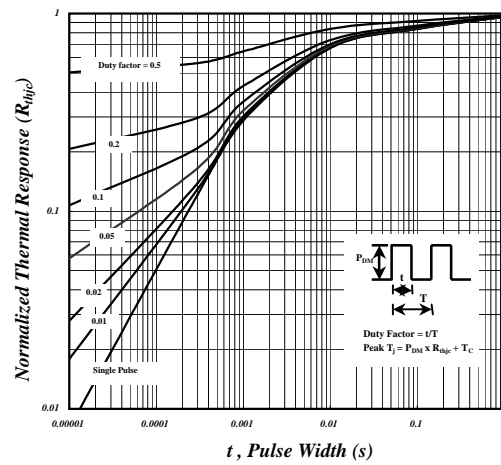


Fig 10. Effective Transient Thermal Impedance

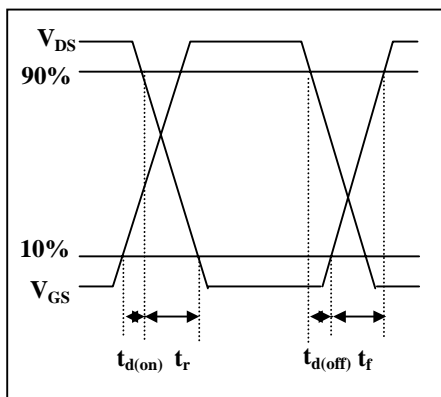


Fig 11. Switching Time Waveform

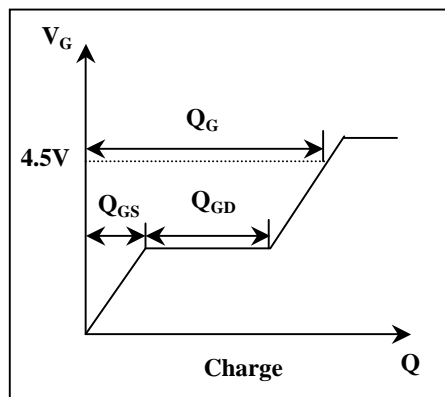
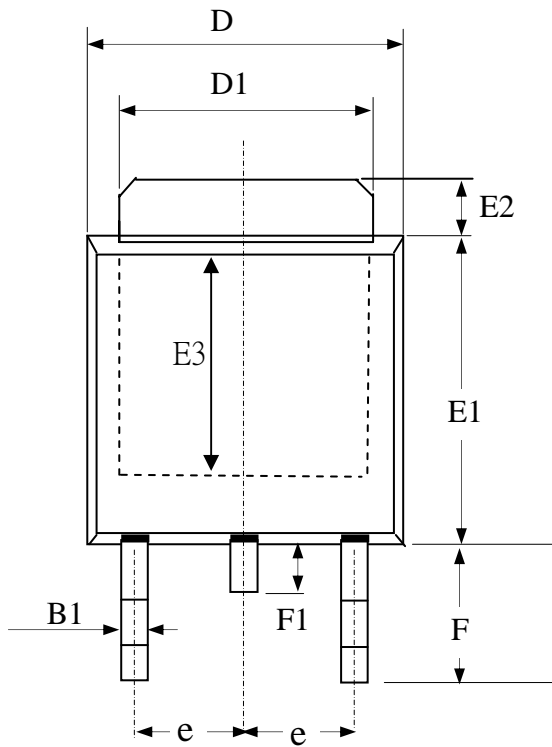


Fig 12. Gate Charge Waveform



Package Outline : TO-252



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.5	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

- 1.All Dimensions Are in Millimeters.
- 2.Dimension Does Not Include Mold Protrusions.



Part Marking Information & Packing : TO-252

